

Yoko Takada

List of Publications by Year in descending order

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10
papers

17
citations

2258059

3
h-index

2272923

4
g-index

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all docs

10
docs citations

10
times ranked

20
citing authors

#	ARTICLE	IF	CITATIONS
1	Highly reliable (Pb,La)(Zr, Ti)O ₃ ; ferroelectric capacitor with sputtered Sn-doped In ₂ O ₃ bottom electrode. , 2018, , .		0
2	Fabrication and electrical properties of a (Pb,La)(Zr,Ti)O ₃ capacitor with pulsed laser deposited Sn-doped In ₂ O ₃ bottom electrode on Al ₂ O ₃ (0001). Japanese Journal of Applied Physics, 2017, 56, 07KC02.	1.5	2
3	Comparative study of ferroelectric (K,Na)NbO ₃ thin films pulsed laser deposition on platinum substrates with different orientation. , 2016, , .		0
4	Evaluation of deuterium ion profile in (Pb,La)(Zr,Ti)O ₃ capacitors structures with conductive oxide top electrode by time of flight secondary ion mass spectrometry. , 2016, , .		0
5	Reliability of the Properties of (Pb,La)(Zr,Ti)O ₃ Capacitors with Non-noble Metal Oxide Electrodes stored in an H ₂ Atmosphere. MRS Advances, 2016, 1, 369-374.	0.9	3
6	Comparative Study of Hydrogen- and Deuterium-Induced Degradation of Ferroelectric (Pb,La)(Zr,Ti)O ₃ Capacitors Using Time-of-Flight Secondary Ion Measurement. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2016, 63, 1668-1673.	3.0	6
7	The effect of H ₂ distribution in (Pb,La)(Zr,Ti)O ₃ capacitors with conductive oxide electrodes on the degradation of ferroelectric properties. Materials Research Society Symposia Proceedings, 2015, 1729, 93-98.	0.1	0
8	The orientation controlled (Pb,La)(Zr,Ti)O ₃ capacitor for improved reliabilities. , 2015, , .		0
9	Hydrogen profile measurement of (Pb,La)(Zr,Ti)O ₃ capacitor with conductive electrode after hydrogen annealing. , 2015, , .		1
10	Aluminum-doped zinc oxide electrode for robust (Pb,La)(Zr,Ti)O ₃ capacitors: effect of oxide insulator encapsulation and oxide buffer layer. Journal of Materials Science: Materials in Electronics, 2014, 25, 2155-2161.	2.2	5